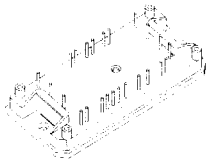
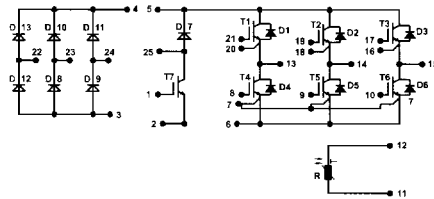


# NPT, CBI IGBT Modules with integrated NTC temperature sense

## Converter - Brake - Inverter Modules

Type	Rectifier * 3~			Inverter 3~					Brake			Package style	
	$V_{RRM}$	$I_{DAVM}$ $T_c = 70^\circ\text{C}$	$R_{thJC}$ typ.	$V_{CES}$	$I_c$ $T_c = 25^\circ\text{C}$	$I_c$ $T_c = 80^\circ\text{C}$	$V_{CE(sat)}$ max.	$R_{thJC}$ typ.	$V_{CES}$	$I_c$ $T_c = 80^\circ\text{C}$	$R_{thJC}$ typ.		
$T_{JM} = 150^\circ\text{C}$	V	A	K/W	V	A	A	V	K/W	V	A	K/W	Fig. No.	
<b>New</b>													
MUBW 6-06A6	1200	9.6	1.9	600	7	5	2.5	3.4	600	5	3.4		49
MUBW 8-06A6		9.6	1.9		8	5.5		2.4		5.5	2.4		
MUBW 10-06A6		9.6	1.9		12	8		2.0		5.5	2.4		
MUBW 15-06A6		9.6	1.9		17	12		1.7		5.5	2.4		
MUBW 25-06A6		29	1.6		25	17		1.7		8	2.0		
MUBW 35-06A6		66	1.35		37	25		1.35		tbd	tbd		
MUBW 4-12A6	1600	9.6	1.9	1200	3.6	2.5	3.3	2.5	1200	2.5	2.5		
MUBW 10-12A6		9.6	1.9		12	8	3.3	1.8		2.5	2.5		
MUBW 15-12A6		29	1.6		14	9	2.9	1.8		8	1.8		
MUBW 30-12A6		66	1.35		32	23	2.6	1.4		9	1.8		

MUBW data preliminary  
\* Single phase input on request

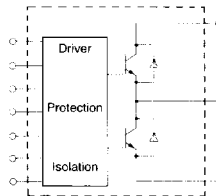



## ISOSMART® IGBT Modules

Intelligent Power Modules (IPM) with integrated galvanic isolation interface

### Features:

- Input logic, isolation, drive circuitry and protection in one package
- ESD protected digital interface
- galvanic isolation, 3 kV<sub>RMS</sub> between logic and power
- optimized gate drive
- short-circuit and under-voltage protection



Type	$V_{CES}$	$I_c$	$I_c$	$V_{CE(sat)}$	$E_{on}$ ①	$E_{off}$	$R_{thJC}$	$P_c$	Package style
	V	$T_c = 25^\circ\text{C}$ A	$T_c = 80^\circ\text{C}$ A	V	typ. 125°C mJ	typ. 125°C mJ	max. K/W	max. W	
<b>High speed</b>	1200	100	90	3.4	24.5	22	0.20	625	Outline page 54 Weight = 270 g 
VIE 100-12S4		125	119	3.7	30	27	0.15	830	
VIE 125-12S4		150	138	3.7	37	37	0.13	950	
VIE 200-12S4		200	168	3.7	50	50	0.11	1100	

①  $E_{on}$  including turn-on energy caused by commutation of free-wheeling diode